

2 to 20 GHz AA220N4-00

GaAs MMIC Distributed Amplifier

Features

- Excellent Broadband Performance
- 6.5 dB Gain, Typical
- E-Beam Written Gates
- On Wafer Probe Pads
- Size 120 x 60 x 4 (mil)

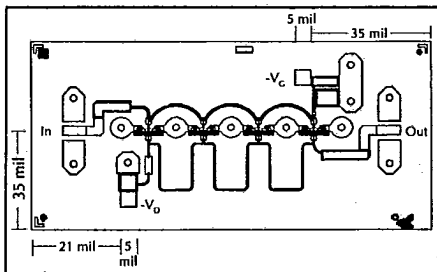
Description

The AA220N4-00 GaAs monolithic distributed amplifier has been designed for superior performance, uniformity, and reliability in broadband gain block applications. Four 0.25 mm x 200 mm MBE grown MESFET devices with E-beam written gates are used for excellent uniformity and reproducibility, with input/output VSWR typically less than 2:1.

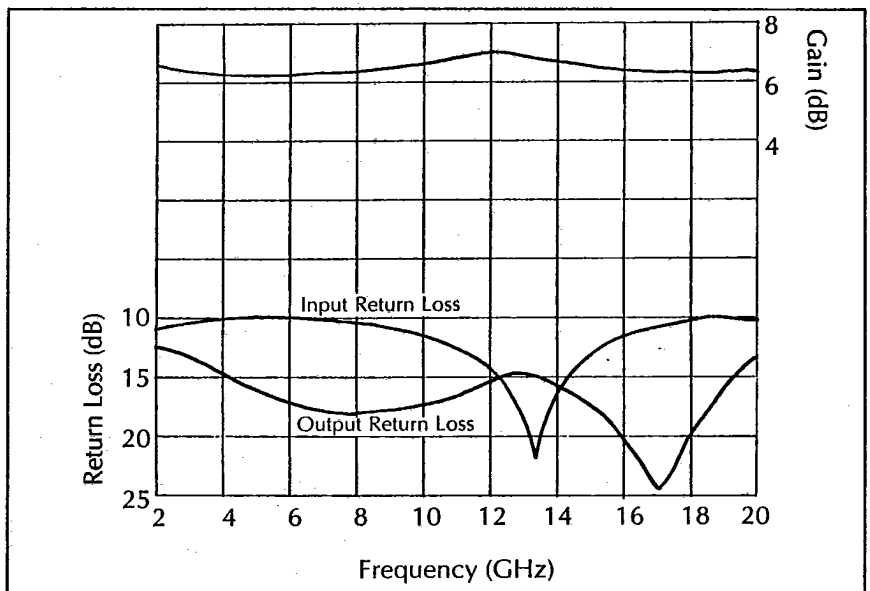
Electrical Specifications

Frequency	2 to 20 GHz
Small Signal Gain	6.5 dB Typ. 6.0 dB Min.
Flatness	±.75 dB, Typ. •1dB, Max.
Input/Output VSWR	2.1 Typ. <2:5 Max.
Noise Figure	7 dB, Typ.
Drain Current, $V_{DD}=8V$	80 mA Typ. 100 mA Max.
P_{1dB}	10 dBm Min.

Chip Configuration



Typical Performance



Specifications subject to change without notice.

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